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74LVC373A

Low-Voltage CMOS Octal Transparent Latch

With 5 V−Tolerant Inputs and Outputs (3−State, Non−Inverting)

The 74LVC373A is a high performance, non−inverting octal transparent latch operating from a 1.2 to 3.6 V supply. High impedance TTL compatible inputs significantly reduce current loading to input drivers while TTL compatible outputs offer improved switching noise performance. A V_I specification of 5.5 V allows 74LVC373A inputs to be safely driven from 5 V devices.

The 74LVC373A contains 8 D−type latches with 3−state outputs. When the Latch Enable (LE) input is HIGH, data on the Dn inputs enters the latches. In this condition, the latches are transparent, i.e., a latch output will change state each time its D input changes. When LE is LOW, the latches store the information that was present on the D inputs a setup time preceding the HIGH−to−LOW transition of LE. The 3−state standard outputs are controlled by the Output Enable ($\overline{OE}$) input. When $\overline{OE}$ is LOW, the standard outputs are enabled. When $\overline{OE}$ is HIGH, the standard outputs are in the high impedance state, but this does not interfere with new data entering into the latches.

Features

- Designed for 1.2 to 3.6 V V_{CC} Operation
- 5 V Tolerant − Interface Capability With 5 V TTL Logic
- Supports Live Insertion and Withdrawal
- I_{OFF} Specification Guarantees High Impedance When V_{CC} = 0 V
- 24 mA Output Sink and Source Capability
- Near Zero Static Supply Current in all Three Logic States (10 μA) Substantially Reduces System Power Requirements
- ESD Performance:
  - Human Body Model >2000 V
  - Machine Model >200 V
- These Devices are Pb−Free, Halogen Free/BFR Free and are RoHS Compliant

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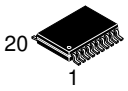
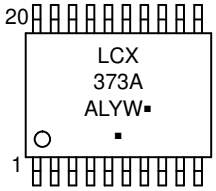
MARKING DIAGRAM



TSSOP−20
DT SUFFIX
CASE 948E



A	= Assembly Location
L, WL	= Wafer Lot
Y, YY	= Year
W, WW	= Work Week
G or ▪	= Pb−Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information on page 8 of this data sheet.

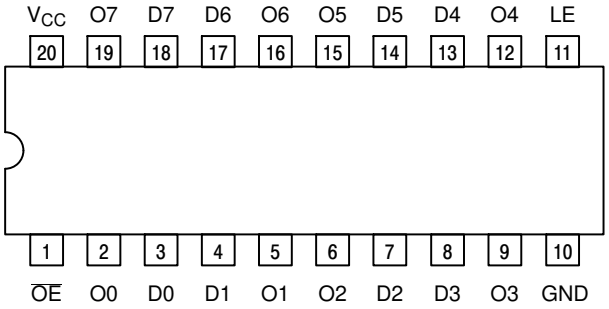


Figure 1. Pinout (Top View)

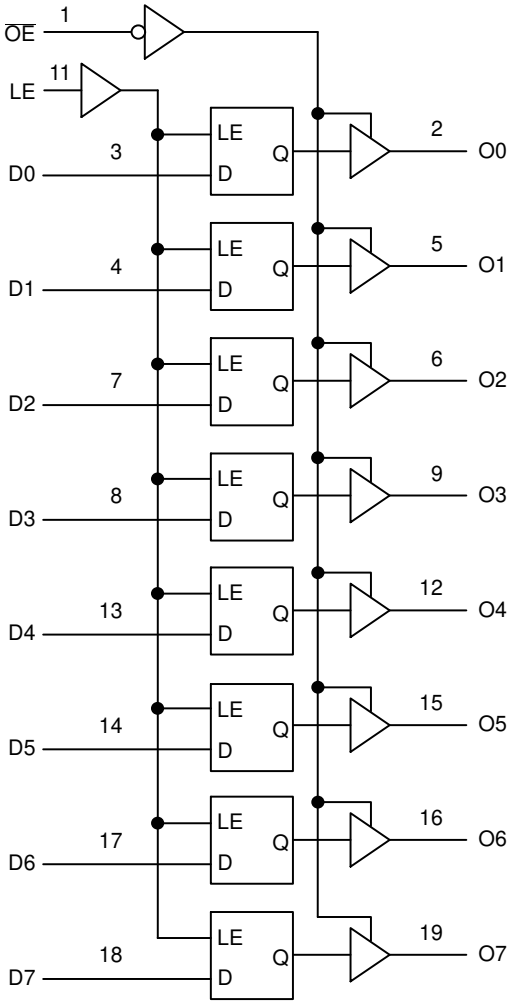


Figure 2. Logic Diagram

PIN NAMES

PINS	FUNCTION
$\overline{OE}$	Output Enable Input
LE	Latch Enable Input
D0–D7	Data Inputs
O0–O7	3–State Latch Outputs

TRUTH TABLE

Inputs			Outputs	Operating Mode
OE	LE	Dn	On	
L L	H H	H L	H L	Transparent (Latch Disabled); Read Latch
L L	L L	h l	H L	Latched (Latch Enabled) Read Latch
L	L	X	NC	Hold; Read Latch
H	L	X	Z	Hold; Disabled Outputs
H H	H H	H L	Z Z	Transparent (Latch Disabled); Disabled Outputs
H H	L L	h l	Z Z	Latched (Latch Enabled); Disabled Outputs

H = High Voltage Level
h = High Voltage Level One Setup Time Prior to the Latch Enable High–to–Low Transition
L = Low Voltage Level
l = Low Voltage Level One Setup Time Prior to the Latch Enable High–to–Low Transition
NC = No Change, State Prior to the Latch Enable High–to–Low Transition
X = High or Low Voltage Level or Transitions are Acceptable
Z = High Impedance State
For I_{CC} Reasons DO NOT FLOAT Inputs

MAXIMUM RATINGS

Symbol	Parameter	Condition	Value	Unit
V_{CC}	DC Supply Voltage		−0.5 to +6.5	V
V_I	DC Input Voltage		$-0.5 \le V_I \le +6.5$	V
V_O	DC Output Voltage	Output in 3−State	$-0.5 \le V_O \le +6.5$	V
		Output in HIGH or LOW State (Note 1)	$-0.5 \le V_O \le V_{CC} + 0.5$	V
I_{IK}	DC Input Diode Current	$V_I < GND$	−50	mA
I_{OK}	DC Output Diode Current	$V_O < GND$	−50	mA
		$V_O > V_{CC}$	+50	mA
I_O	DC Output Source/Sink Current		±50	mA
I_{CC}	DC Supply Current Per Supply Pin		±100	mA
I_{GND}	DC Ground Current Per Ground Pin		±100	mA
T_{STG}	Storage Temperature Range		−65 to +150	°C
T_L	Lead Temperature, 1 mm from Case for 10 Seconds		T_L = 260	°C
T_J	Junction Temperature Under Bias		T_J = 135	°C
θ_{JA}	Thermal Resistance (Note 2)		110.7	°C/W
MSL	Moisture Sensitivity	Level 1		

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. I_O absolute maximum rating must be observed.
2. Measured with minimum pad spacing on an FR4 board, using 10 mm−by−1 inch, 2 ounce copper trace no air flow.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Typ	Max	Unit
V_{CC}	Supply Voltage Operating Functional	1.65 1.2		3.6 3.6	V
V_I	Input Voltage	0		5.5	V
V_O	Output Voltage HIGH or LOW State 3−State	 0 0		 V_{CC} 5.5	V
I_{OH}	HIGH Level Output Current V_{CC} = 3.0 V – 3.6 V V_{CC} = 2.7 V – 3.0 V			 −24 −12	mA
I_{OL}	LOW Level Output Current V_{CC} = 3.0 V – 3.6 V V_{CC} = 2.7 V – 3.0 V			 24 12	mA
T_A	Operating Free−Air Temperature	−40		+125	°C
$\Delta t/\Delta V$	Input Transition Rise or Fall Rate, V_{CC} = 1.65 to 2.7 V V_{CC} = 2.7 to 3.6 V	 0 0		 20 10	ns/V

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

DC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Conditions	–40 to +85°C			–40 to +125°C			Unit
			Min	Typ (Note 3)	Max	Min	Typ (Note 3)	Max	
V_{IH}	HIGH–level input voltage	V_{CC} = 1.2 V	1.08	–	–	1.08	–	–	V
		V_{CC} = 1.65 V to 1.95 V	0.65 x V_{CC}	–	–	0.65 x V_{CC}	–	–	
		V_{CC} = 2.3 V to 2.7 V	1.7	–	–	1.7	–	–	
		V_{CC} = 2.7 V to 3.6 V	2.0	–	–	2.0	–	–	
V_{IL}	LOW–level input voltage	V_{CC} = 1.2 V	–	–	0.12	–	–	0.12	V
		V_{CC} = 1.65 V to 1.95 V	–	–	0.35 x V_{CC}	–	–	0.35 x V_{CC}	
		V_{CC} = 2.3 V to 2.7 V	–	–	0.7	–	–	0.7	
		V_{CC} = 2.7 V to 3.6 V	–	–	0.8	–	–	0.8	
V_{OH}	HIGH–level output voltage	V_I = V_{IH} or V_{IL}							V
		I_O = –100 μA; V_{CC} = 1.65 V to 3.6 V	V_{CC} – 0.2	–	–	V_{CC} – 0.3	–	–	
		I_O = –4 mA; V_{CC} = 1.65 V	1.2	–	–	1.05	–	–	
		I_O = –8 mA; V_{CC} = 2.3 V	1.8	–	–	1.65	–	–	
		I_O = –12 mA; V_{CC} = 2.7 V	2.2	–	–	2.05	–	–	
		I_O = –18 mA; V_{CC} = 3.0 V	2.4	–	–	2.25	–	–	
		I_O = –24 mA; V_{CC} = 3.0 V	2.2	–	–	2.0	–	–	
V_{OL}	LOW–level output voltage	V_I = V_{IH} or V_{IL}							V
		I_O = 100 μA; V_{CC} = 1.65 V to 3.6 V	–	–	0.2	–	–	0.3	
		I_O = 4 mA; V_{CC} = 1.65 V	–	–	0.45	–	–	0.65	
		I_O = 8 mA; V_{CC} = 2.3 V	–	–	0.6	–	–	0.8	
		I_O = 12 mA; V_{CC} = 2.7 V	–	–	0.4	–	–	0.6	
		I_O = 24 mA; V_{CC} = 3.0 V	–	–	0.55	–	–	0.8	
I_I	Input leakage current	V_I = 5.5 V or GND; V_{CC} = 3.6 V	–	±0.1	±5	–	±0.1	±20	μA
I_{OZ}	OFF–state output current	VI = VIH or VIL; V_O = 5.5 V or GND; V_{CC} = 3.6 V	–	±0.1	±5	–	±0.1	±20	μA
I_{OFF}	Power–off leakage current	V_I or V_O = 5.5 V; V_{CC} = 0.0 V	–	±0.1	±10	–	±0.1	±20	μA
I_{CC}	Supply current	V_I = V_{CC} or GND; I_O = 0 A; V_{CC} = 3.6 V	–	0.1	10	–	0.1	40	μA
ΔI_{CC}	Additional supply current	per input pin; V_I = V_{CC} – 0.6 V; I_O = 0 A; V_{CC} = 2.7 V to 3.6 V	–	5	500	–	5	5000	μA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

3. All typical values are measured at T_A = 25°C and V_{CC} = 3.3 V, unless stated otherwise.

AC ELECTRICAL CHARACTERISTICS ($t_R = t_F$ = 2.5 ns)

Symbol	Parameter	Conditions	–40 to +85°C			–40 to +125°C			Unit
			Min	Typ (Note 4)	Max	Min	Typ (Note 4)	Max	
t_{pd}	Propagation Delay (Note 5) Dn to On	V_{CC} = 1.2 V	–	14.0	–	–	–	–	ns
		V_{CC} = 1.65 V to 1.95 V	1.5	6.5	15.8	1.5	–	18.2	
		V_{CC} = 2.3 V to 2.7 V	1.0	3.4	8.2	1.0	–	9.4	
		V_{CC} = 2.7 V	1.5	3.4	7.8	1.5	–	10.0	
		V_{CC} = 3.0 V to 3.6 V	1.5	2.9	6.8	1.5	–	8.5	
t_{pd}	Propagation Delay LE to On	V_{CC} = 1.2 V	–	16.0	–	–	–	–	ns
		V_{CC} = 1.65 V to 1.95 V	2.2	7.3	16.8	2.2	–	19.3	
		V_{CC} = 2.3 V to 2.7 V	1.5	3.9	8.6	1.5	–	10.0	
		V_{CC} = 2.7 V	1.5	3.5	8.2	1.5	–	10.5	
		V_{CC} = 3.0 V to 3.6 V	1.5	3.3	7.2	1.5	–	9.0	
t_{en}	Enable Time (Note 6) $\overline{OE}$ to On	V_{CC} = 1.2 V	–	17.0	–	–	–	–	ns
		V_{CC} = 1.65 V to 1.95 V	1.5	6.8	17.6	1.5	–	20.3	
		V_{CC} = 2.3 V to 2.7 V	1.5	3.8	9.7	1.5	–	11.2	
		V_{CC} = 2.7 V	1.5	3.8	8.7	1.5	–	11.0	
		V_{CC} = 3.0 V to 3.6 V	1.5	3.1	7.7	1.5	–	10.0	
t_{dis}	Disable Time (Note 7) $\overline{OE}$ to On	V_{CC} = 1.2 V	–	8.0	–	–	–	–	ns
		V_{CC} = 1.65 V to 1.95 V	1.5	4.3	10.3	1.5	–	11.9	
		V_{CC} = 2.3 V to 2.7 V	1.0	2.4	5.8	1.0	–	6.8	
		V_{CC} = 2.7 V	1.5	3.2	7.1	1.5	–	9.0	
		V_{CC} = 3.0 V to 3.6 V	1.5	3.0	6.1	1.5	–	8.0	
t_w	Pulse Width LE HIGH	V_{CC} = 1.65 V to 1.95 V	5.0	–	–	5.0	–	–	ns
		V_{CC} = 2.3 V to 2.7 V	4.0	–	–	4.0	–	–	
		V_{CC} = 2.7 V	3.0	–	–	3.0	–	–	ns
		V_{CC} = 3.0 V to 3.6 V	3.0	1.5	–	3.0	–	–	
t_{su}	Set–up Time On to LE	V_{CC} = 1.65 V to 1.95 V	4.0	–	–	4.0	–	–	ns
		V_{CC} = 2.3 V to 2.7 V	3.0	–	–	3.0	–	–	
		V_{CC} = 2.7 V	2.0	–	–	2.0	–	–	
		V_{CC} = 3.0 V to 3.6 V	2.0	0.0	–	2.0	–	–	
t_h	Hold Time On to LE	V_{CC} = 1.65 V to 1.95 V	3.0	–	–	3.0	–	–	ns
		V_{CC} = 2.3 V to 2.7 V	2.0	–	–	2.0	–	–	
		V_{CC} = 2.7 V	1.5	–	–	1.5	–	–	
		V_{CC} = 3.0 V to 3.6 V	1.5	0.3	–	1.5	–	–	
$t_{sk(0)}$	Output Skew Time (Note 8)		–	–	1.0	–	–	1.5	ns

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. Typical values are measured at T_A = 25°C and V_{CC} = 3.3 V, unless stated otherwise.
5. t_{pd} is the same as t_{PLH} and t_{PHL}.
6. t_{en} is the same as t_{PZL} and t_{PZH}.
7. t_{dis} is the same as t_{PLZ} and t_{PHZ}.
8. Skew between any two outputs of the same package switching in the same direction. This parameter is guaranteed by design.

DYNAMIC SWITCHING CHARACTERISTICS

Symbol	Characteristic	Condition	T_A = +25°C			Unit
			Min	Typ	Max	
V_{OLP}	Dynamic LOW Peak Voltage (Note 9)	V_{CC} = 3.3 V, C_L = 50 pF, V_{IH} = 3.3 V, V_{IL} = 0 V V_{CC} = 2.5 V, C_L = 30 pF, V_{IH} = 2.5 V, V_{IL} = 0 V		0.8 0.6		V
V_{OLV}	Dynamic LOW Valley Voltage (Note 9)	V_{CC} = 3.3 V, C_L = 50 pF, V_{IH} = 3.3 V, V_{IL} = 0 V V_{CC} = 2.5 V, C_L = 30 pF, V_{IH} = 2.5 V, V_{IL} = 0 V		–0.8 –0.6		V

9. Number of outputs defined as “n”. Measured with “n–1” outputs switching from HIGH–to–LOW or LOW–to–HIGH. The remaining output is measured in the LOW state.

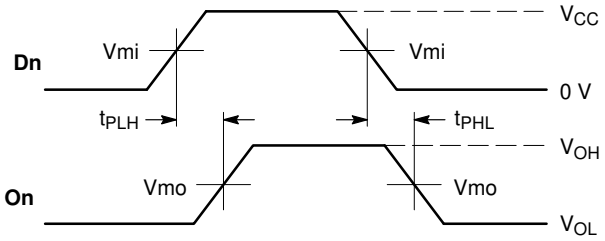
CAPACITIVE CHARACTERISTICS

Symbol	Parameter	Condition	Typical	Unit
C_{IN}	Input Capacitance	V_{CC} = 3.3 V, V_I = 0 V or V_{CC}	5.0	pF
C_{OUT}	Output Capacitance	V_{CC} = 3.3 V, V_I = 0 V or V_{CC}	6.0	pF
C_{PD}	Power Dissipation Capacitance (Note 10)	Per flip–flop; V_I = GND or V_{CC}		pF
		V_{CC} = 1.65 V to 1.95 V	16.6	
		V_{CC} = 2.3 V to 2.7 V	19.2	
		V_{CC} = 3.0 V to 3.6 V	21.6	

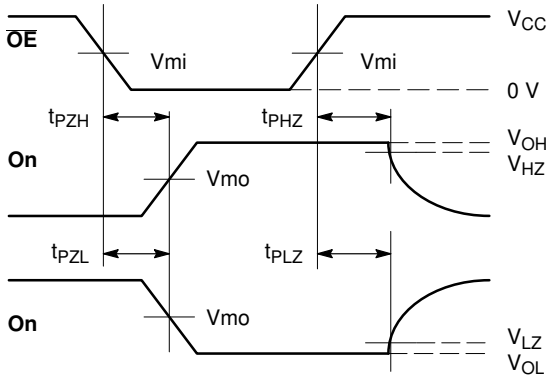
10. C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

$$P_D = C_{PD} \times V_{CC}{}^2 \times fi \times N + \Sigma\left(C_L \times V_{CC}{}^2 \times fo\right) \text{ where:}$$

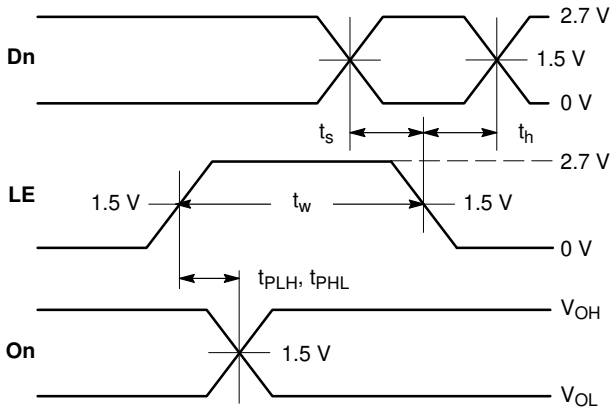
fi = input frequency in MHz; fo = output frequency in MHz
C_L = output load capacitance in pF
V_{CC} = supply voltage in Volts
N = number of outputs switching
$\Sigma(C_L \times V_{CC}{}^2 \times fo)$ = sum of the outputs



WAVEFORM 1 – PROPAGATION DELAYS
$t_R = t_F$ = 2.5 ns, 10% to 90%; f = 1 MHz; t_W = 500 ns



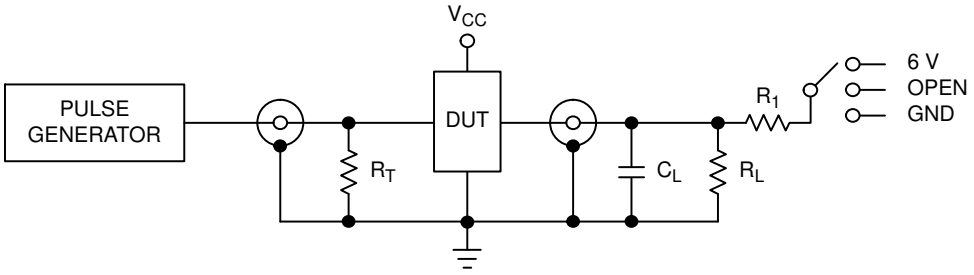
WAVEFORM 2 – OUTPUT ENABLE AND DISABLE TIMES
$t_R = t_F$ = 2.5 ns, 10% to 90%; f = 1 MHz; t_W = 500 ns



Symbol	V_{CC}		
	3.3 V ± 0.3 V	**2.7 V**	**V_{CC} < 2.7 V**
Vmi	1.5 V	1.5 V	$V_{CC}/2$
Vmo	1.5 V	1.5 V	$V_{CC}/2$
V_{HZ}	V_{OL} + 0.3 V	V_{OL} + 0.3 V	V_{OL} + 0.15 V
V_{LZ}	V_{OH} – 0.3 V	V_{OH} – 0.3 V	V_{OH} – 015 V

WAVEFORM 3 – LE to On PROPAGATION DELAYS, LE MINIMUM PULSE WIDTH, Dn to LE SETUP AND HOLD TIMES
$t_R = t_F$ = 2.5 ns, 10% to 90%; f = 1 MHz; t_W = 500 ns except when noted

Figure 3. AC Waveforms



C_L includes jig and probe capacitance
$R_T = Z_{OUT}$ of pulse generator (typically 50 Ω)
$R_1 = R_L$

Supply Voltage	Input		Load		VEXT		
V_{CC} (V)	V_I	t_r, t_f	C_L	R_L	tPLH, tPHL	tPLZ, tPZL	tPHZ, tPZH
1.2	V_{CC}	≤ 2 ns	30 pF	1 kΩ	Open	2 x V_{CC}	GND
1.65 – 1.95	V_{CC}	≤ 2 ns	30 pF	1 kΩ	Open	2 x V_{CC}	GND
2.3 – 2.7	V_{CC}	≤ 2 ns	30 pF	500 Ω	Open	2 x V_{CC}	GND
2.7	2.7 V	≤ 2.5 ns	50 pF	500 Ω	Open	2 x V_{CC}	GND
3.0 – 3.6	2.7 V	≤ 2.5 ns	50 pF	500 Ω	Open	2 x V_{CC}	GND

Figure 4. Test Circuit

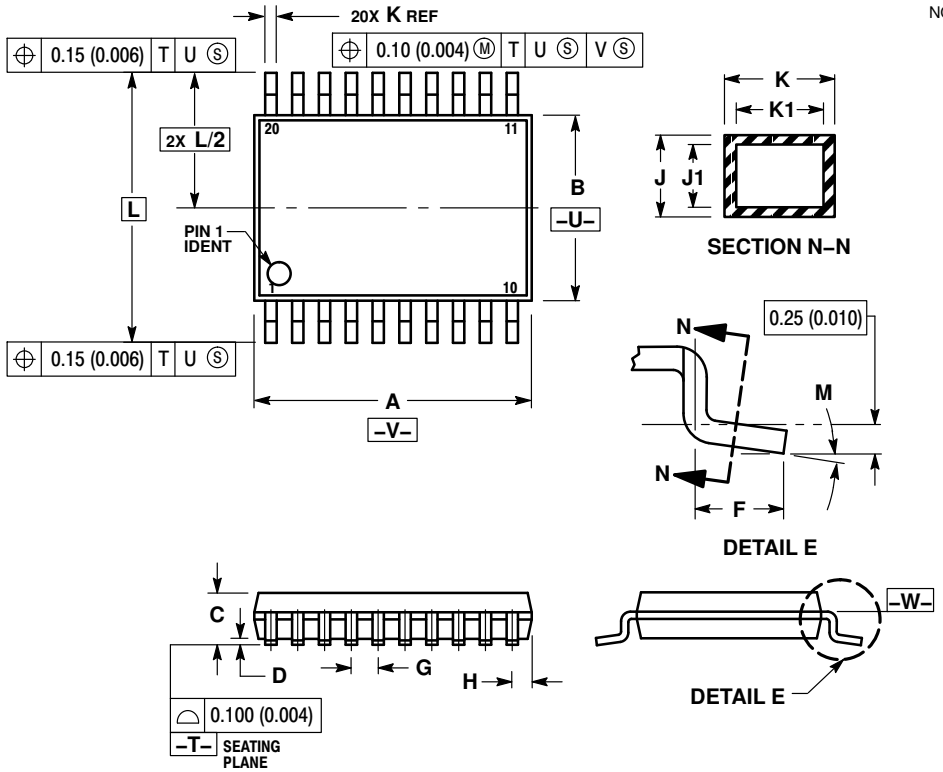
ORDERING INFORMATION

Device	Package	Shipping†
74LVC373ADTR2G	TSSOP–20 (Pb–Free)	2500 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

PACKAGE DIMENSIONS

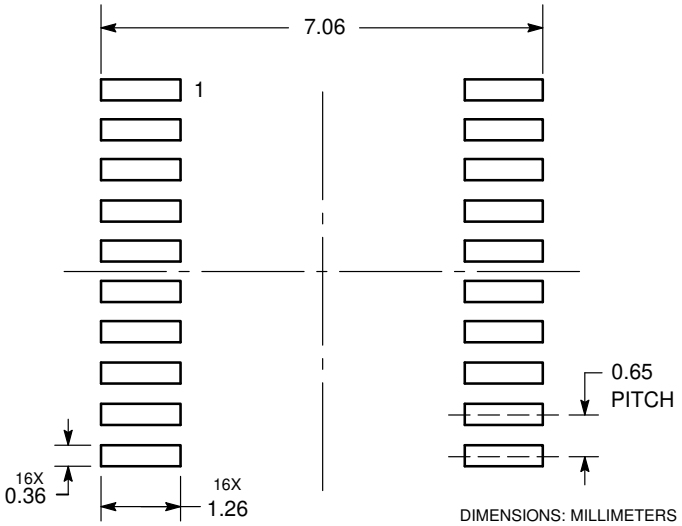
TSSOP–20
DT SUFFIX
CASE 948E–02
ISSUE C



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE –W–.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	6.40	6.60	0.252	0.260
B	4.30	4.50	0.169	0.177
C	---	1.20	---	0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
H	0.27	0.37	0.011	0.015
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252 BSC	
M	0°	8°	0°	8°

SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PUBLICATION ORDERING INFORMATION

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